

**NTE376**  
**Silicon NPN Transistor**  
**TV Power Supply Driver/Audio Output**

**Absolute Maximum Ratings:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Collector–Base Voltage, $V_{CBO}$ .....	300V
Collector–Emitter Voltage, $V_{CEO}$ .....	300V
Emitter–Base Voltage, $V_{EBO}$ .....	5V
Collector Current, $I_C$ .....	200mA
Power Dissipation, $P_C$ .....	15W
Operating Junction Temperature, $T_j$ .....	+150°C
Storage Temperature Range, $T_{stg}$ .....	–45° to +150°C

**Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	300	–	–	V
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 5\text{mA}, R_{BE} = \infty$	300	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}, I_C = 0$	5	–	–	V
Collector–Base Current	$I_{CBO}$	$V_{CB} = 250\text{V}, I_E = 0$	–	–	0.1	$\mu\text{A}$
Collector–Emitter Current	$I_{CEO}$	$V_{CE} = 250\text{V}, R_{BE} = \infty$	–	–	2	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE} = 10\text{V}, I_C = 50\text{mA}$	40	–	200	–
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 100\text{mA}, I_B = 10\text{mA}$	–	0.32	1.5	V
Base–Emitter Voltage	$V_{BE}$	$V_{CE} = 10\text{V}, I_C = 50\text{mA}$	–	0.66	0.9	V
Current Gain–Bandwidth Product	$f_T$	$V_{CE} = 20\text{V}, I_C = 30\text{mA}$	60	70	–	MHz
Collector–Base Capacitance	$C_{ob}$	$V_{CB} = 50\text{V}, I_E = 0, f = 1\text{MHz}$	–	6.2	8	pF

